



BYV10ED-600P

Ultrafast power diode

24 July 2015

Product data sheet

1. General description

Enhanced ultrafast power diode in a SOT428 (DPAK) plastic package.

2. Features and benefits

- High thermal cycling performance
- Soft recovery characteristic
- Low on-state losses
- Surface-mountable package
- Low thermal resistance
- Enhanced avalanche energy capability

3. Applications

- Dual Mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology

4. Quick reference data

Table 1. Quick reference data

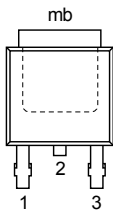
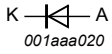
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_{mb} \leq 118$ °C; Square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	10	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25$ μ s; $T_{mb} \leq 118$ °C; Square-wave pulse	-	-	20	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10$ ms; $T_{j(init)} = 25$ °C; SIN; Fig. 4	-	-	70	A
		$t_p = 8.3$ ms; $T_{j(init)} = 25$ °C; SIN; Fig. 4	-	-	80	A
Static characteristics						
V_F	forward voltage	$I_F = 10$ A; $T_j = 25$ °C; Fig. 6	-	1.5	2	V
		$I_F = 10$ A; $T_j = 150$ °C; Fig. 6	-	-	1.6	V
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1$ A; $V_R = 30$ V; $di_F/dt = 50$ A/ μ s; $T_j = 25$ °C; Fig. 7	-	35	50	ns



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	50	-	ns
		$I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 7	-	78	-	ns
Avalanche energy						
E_{AS}	non-repetitive avalanche energy	$I_R = 2.6\text{ A}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; $L = 15\text{ mH}$	-	50	-	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	 <p style="text-align: center;">DPAK (SOT428)</p>	
2	K	cathode ^[1]		
3	A	anode		
mb	K	mounting base; connected to cathode		

[1] It is not possible to connect to pin 2 of the SOT428 package.

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV10ED-600P	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

7. Marking

Table 4. Marking codes

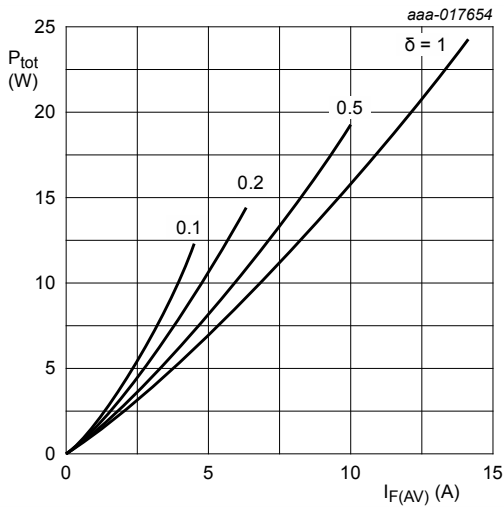
Type number	Marking code
BYV10ED-600P	BYV10ED-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

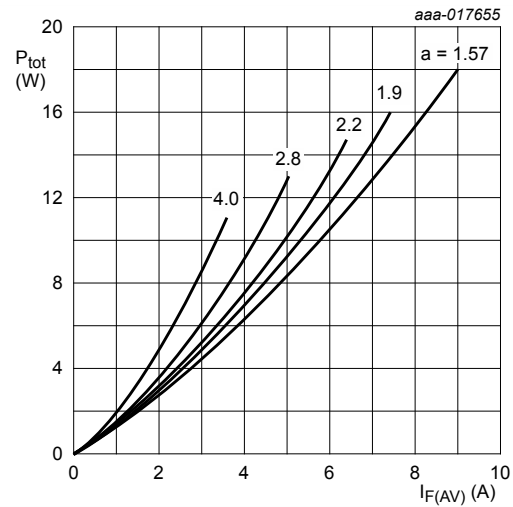
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_{mb} \leq 118$ °C; Square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	10	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25$ μ s; $T_{mb} \leq 118$ °C; Square-wave pulse	-	20	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10$ ms; $T_{j(init)} = 25$ °C; SIN; Fig. 4	-	70	A
		$t_p = 8.3$ ms; $T_{j(init)} = 25$ °C; SIN; Fig. 4	-	80	A
T_{stg}	storage temperature		-40	175	°C
T_j	junction temperature		-	175	°C



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.241 \text{ V}; R_s = 0.034 \text{ } \Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_o = 1.241 \text{ V}; R_s = 0.034 \text{ } \Omega$$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

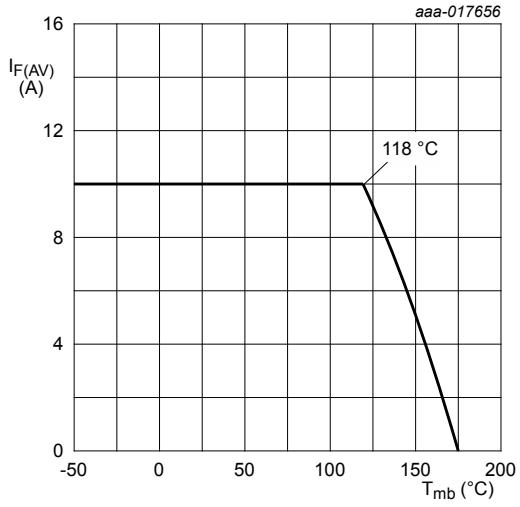


Fig. 3. Forward current as a function of mounting base temperature; maximum values

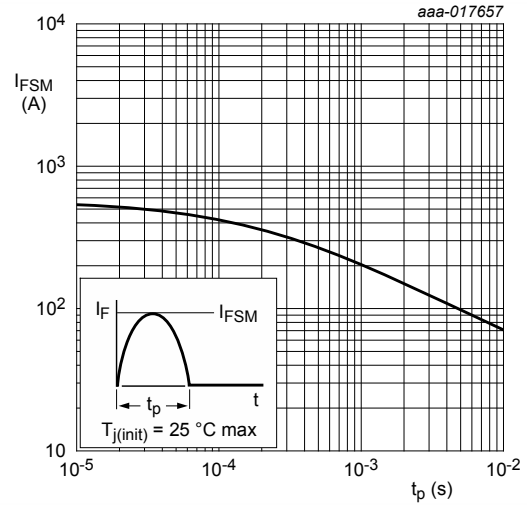


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	With heatsink compound; Fig. 5	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W

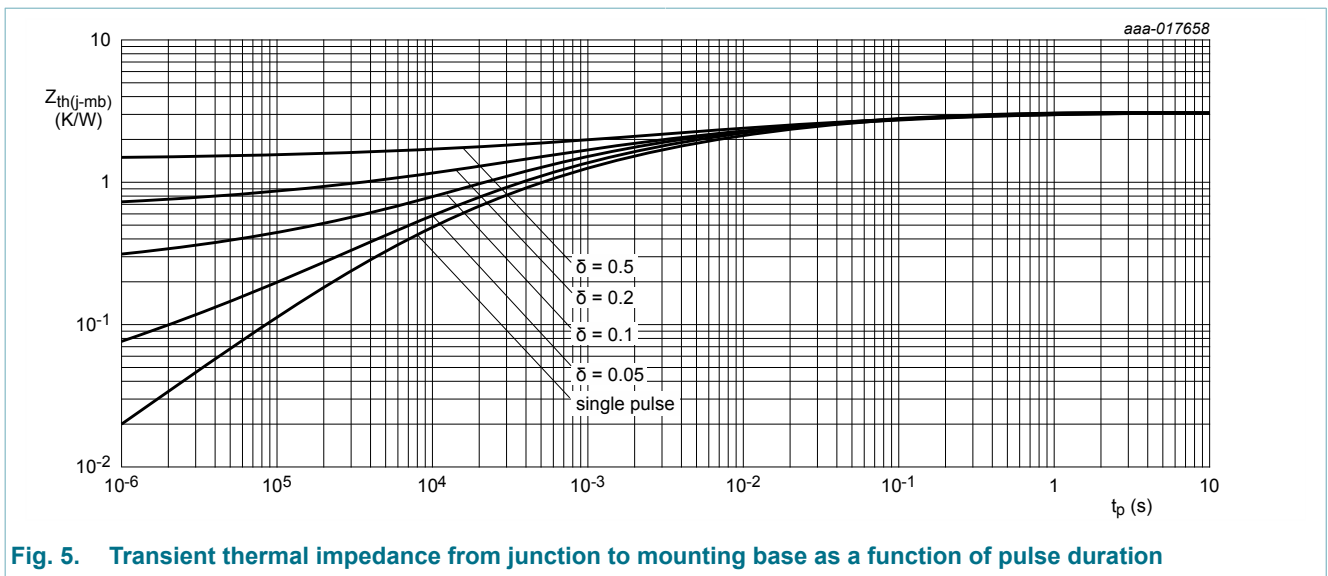
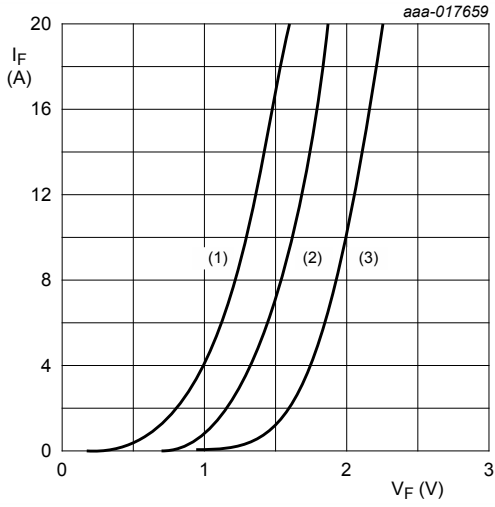


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 10\text{ A}$; $T_j = 25\text{ °C}$; Fig. 6	-	1.5	2	V
		$I_F = 10\text{ A}$; $T_j = 150\text{ °C}$; Fig. 6	-	-	1.6	V
I_R	reverse current	$V_R = 600\text{ V}$; $T_j = 25\text{ °C}$	-	-	10	μA
		$V_R = 600\text{ V}$; $T_j = 150\text{ °C}$	-	-	500	μA
Dynamic characteristics						
Q_r	recovered charge	$I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7	-	123	-	nC
		$I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ °C}$; Fig. 7	-	305	-	nC
t_{rr}	reverse recovery time	$I_F = 1\text{ A}$; $V_R = 30\text{ V}$; $di_F/dt = 50\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7	-	35	50	ns
		$I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7	-	50	-	ns
		$I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ °C}$; Fig. 7	-	78	-	ns
I_{RM}	peak reverse recovery current	$I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7	-	4.9	-	A
		$I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ °C}$; Fig. 7	-	7.8	-	A
Avalanche energy						
E_{AS}	non-repetitive avalanche energy	$I_R = 2.6\text{ A}$; $T_{j(\text{init})} = 25\text{ °C}$; $L = 15\text{ mH}$	-	50	-	mJ



$V_o = 1.241 \text{ V}; R_s = 0.034 \Omega$

- (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 6. Forward current as a function of forward voltage

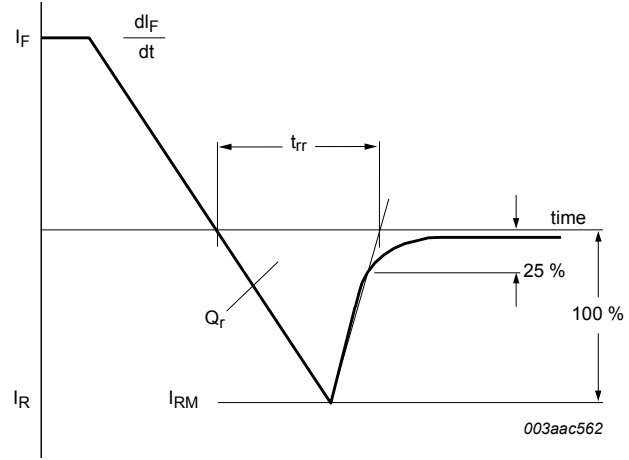
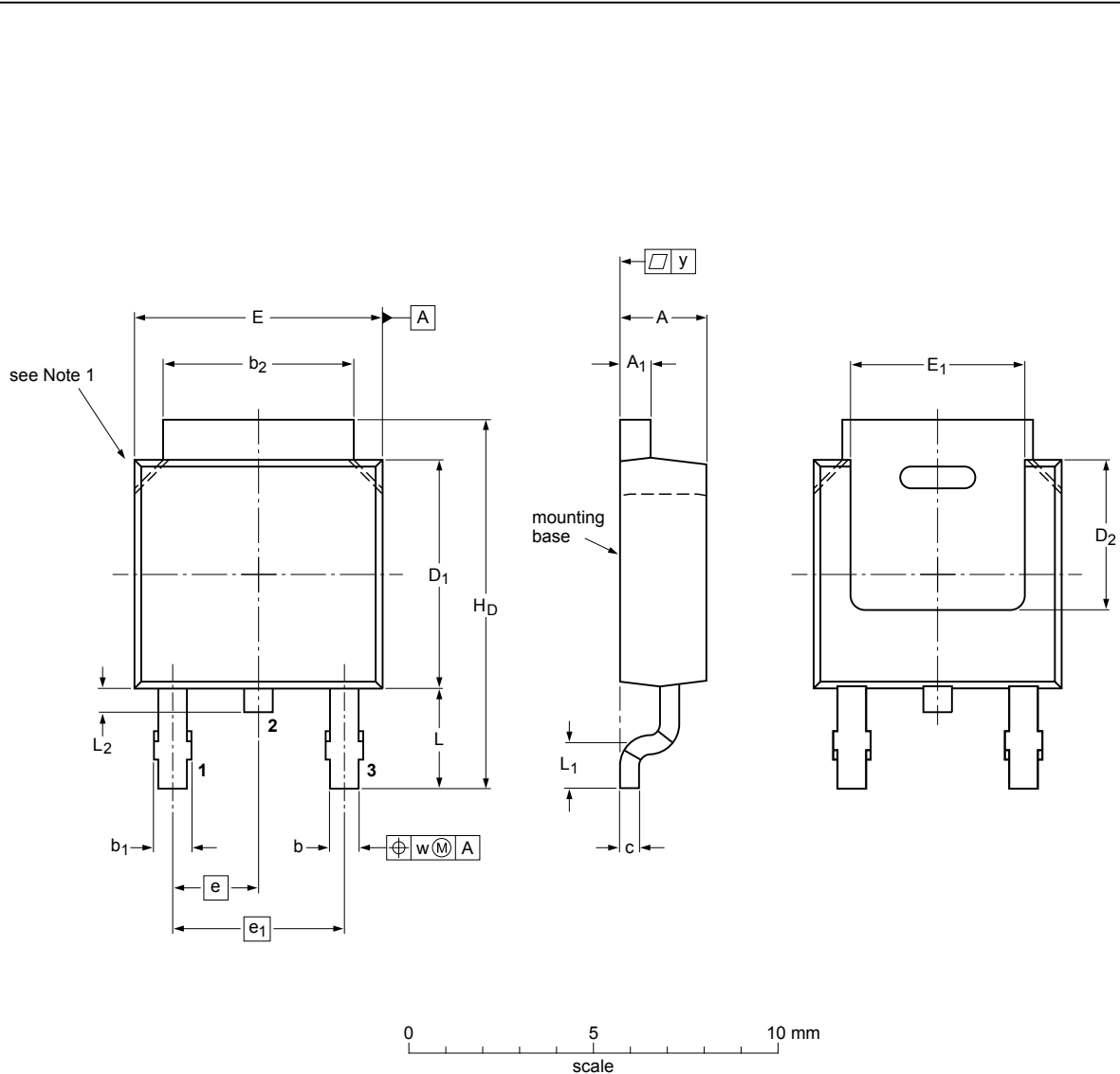


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) SOT428



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	b ₁	b ₂	c	D ₁	D ₂	E	E ₁	e	e ₁	H _D	L	L ₁	L ₂	w	y
max	2.38	0.93	0.89	1.1	5.46	0.56	6.22		6.73				10.4	2.95		0.9		0.2
nom											2.285	4.57					0.2	
min	2.22	0.46	0.71	0.9	5.00	0.20	5.98	4.0	6.47	4.45			9.6	2.55	0.5	0.5		

Note

1. Plastic body may have 45° chamfer.

sot428_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOT428		TO-252	SC-63		06-03-16 14-06-10

Fig. 8. Package outline DPAK (SOT428)

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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